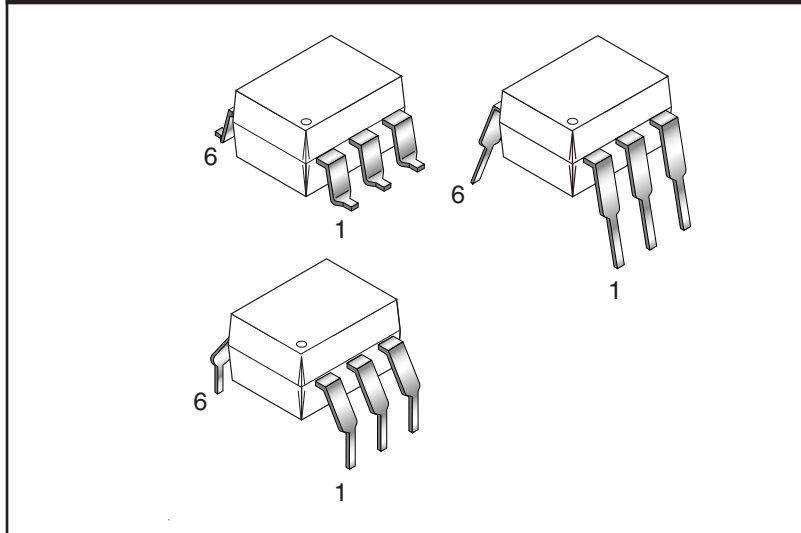


H11N1-M

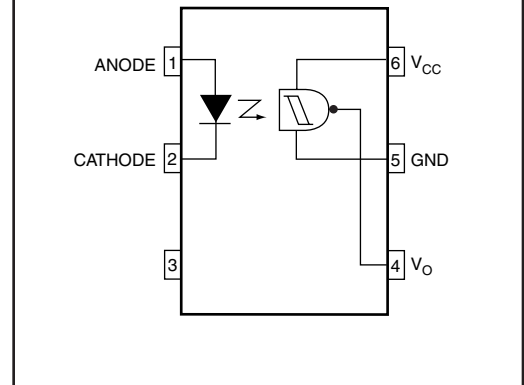
H11N2-M

H11N3-M

PACKAGE



SCHEMATIC



DESCRIPTION

The H11NX-M series has a high speed integrated circuit detector optically coupled to an AlGaAs infrared emitting diode. The output incorporates a Schmitt trigger, which provides hysteresis for noise immunity and pulse shaping. The detector circuit is optimized for simplicity of operation and utilizes an open collector output for maximum application flexibility.

Truth Table

| Input | Output |
|-------|--------|
| H | L |
| L | H |

FEATURES

- High data rate, 5 MHz typical (NRZ)
- Free from latch up and oscillation throughout voltage and temperature ranges.
- Microprocessor compatible drive
- Logic compatible output sinks 16 mA at 0.5 V maximum
- Guaranteed on/off threshold hysteresis
- Wide supply voltage capability, compatible with all popular logic systems
- High common mode transient immunity, 2000 V/ μ s minimum
- Fast switching $t_r = 7.5$ ns typical, $t_f = 12$ ns typical
- Underwriter Laboratory (UL) recognized—file #E90700
- VDE recognized – File#102497 – Add option V (e.g., H11N1VM)

APPLICATIONS

- Logic to logic isolator
- Programmable current level sensor
- Line receiver—eliminate noise and transient problems
- A.C. to TTL conversion—square wave shaping
- Interfaces computers with peripherals
- Isolated power MOS driver for power supplies

H11N1-M

H11N2-M

H11N3-M

ABSOLUTE MAXIMUM RATINGS

| Parameters | Symbol | Device | Value | Units |
|---|-------------|--------|----------------|-------------|
| TOTAL DEVICE | | | | |
| Storage Temperature | T_{STG} | All | -55 to +150 | °C |
| Operating Temperature | T_{OPR} | All | -40 to +85 | °C |
| Lead Solder Temperature | T_{SOL} | All | 260 for 10 sec | °C |
| Total Device Power Dissipation @ 25°C Derate Above 25°C | P_D | All | 250 2.94 | mW mW/°C |
| EMITTER | | | | |
| Continuous Forward Current | I_F | All | 30 | mA |
| Reverse Voltage | V_R | All | 6 | V |
| Forward Current - Peak (1 μ s pulse, 300 pps) | $I_{F(pk)}$ | All | 1.0 | A |
| LED Power Dissipation 25°C Ambient Derate Linearly From 25°C | P_D | All | 120 1.41 | mW mW/°C |
| DETECTOR | | | | |
| Detector Power Dissipation @ 25°C Derate Linearly from 25°C | P_D | All | 150 1.76 | mW mW/°C |
| V_{45} Allowed Range | V_O | All | 0 to 16 | V |
| V_{65} Allowed Range | V_{CC} | All | 0 to 16 | V |
| I_4 Output Current | I_O | All | 50 | mA |

ELECTRICAL CHARACTERISTICS ($T_A = 0-70^\circ\text{C}$ Unless otherwise specified.)

INDIVIDUAL COMPONENT CHARACTERISTICS

| Parameters | Test Conditions | Symbol | Device | Min | Typ* | Max | Units |
|-------------------------|---|---------------|--------|------|------|-----|---------------|
| EMITTER | | | | | | | |
| Input Forward Voltage | $I_F = 10\text{ mA}$ | V_F | All | | 1.4 | 2 | V |
| | $I_F = 0.3\text{ mA}$ | | | 0.75 | 1.25 | | |
| Reverse Current | $V_R = 5\text{ V}$ | I_R | All | | | 10 | μA |
| Capacitance | $V = 0, f = 1.0\text{ MHz}$ | C_J | All | | | 100 | pF |
| DETECTOR | | | | | | | |
| Operating Voltage Range | | V_{CC} | All | 4 | | 15 | V |
| Supply Current | $I_F = 0, V_{CC} = 5\text{ V}$ | $I_{CC(off)}$ | All | | 6 | 10 | mA |
| Output Current, High | $I_F = 0.3\text{ mA}, V_{CC} = V_O = 15\text{ V}$ | I_{OH} | All | | | 100 | μA |

*Typical values at $T_A = 25^\circ\text{C}$

H11N1-M

H11N2-M

H11N3-M

| TRANSFER CHARACTERISTICS | | | | | | | |
|------------------------------------|---|------------------------|---------|------|------|------|-------|
| DC Characteristics | Test Conditions | Symbol | Device | Min | Typ* | Max | Units |
| Supply Current | $I_F = 10\text{mA}, V_{CC} = 5\text{V}$ | $I_{CC(on)}$ | All | | 6.5 | 10 | mA |
| Output Voltage, low | $R_L = 270\Omega, V_{CC} = 5\text{V}, I_F = I_{F(on)} \text{ max.}$ | V_{OL} | All | | | 0.5 | V |
| Turn-On Threshold Current | $R_L = 270\Omega, V_{CC} = 5\text{V}$ note 1 | $I_{F(on)}$ | H11N1-M | 0.8 | | 3.2 | mA |
| | | | H11N2-M | 2.3 | | 5 | |
| | | | H11N3-M | 4.1 | | 10 | |
| Turn-Off Threshold Current | $R_L = 270\Omega, V_{CC} = 5\text{V}$ | $I_{F(off)}$ | All | 0.3 | | | mA |
| Hysteresis Ratio | $R_L = 270\Omega, V_{CC} = 5\text{V}$ | $I_{F(off)}/I_{F(on)}$ | All | 0.65 | | 0.95 | |
| AC Characteristics | Test Conditions | Symbol | Device | Min | Typ | Max | Units |
| SWITCHING SPEED | | | | | | | |
| Propagation delay time High to Low | $C = 120\text{pF}, t_p = 1\mu\text{s}, R_E$: Note 2 Fig. 1 | t_{PHL} | All | | 100 | 330 | ns |
| Rise Time | $C = 120\text{pF}, t_p = 1\mu\text{s}, R_E$: Note 2 Fig. 1 | t_r | All | | 7.5 | | ns |
| Propagation delay time Low to High | $C = 120\text{pF}, t_p = 1\mu\text{s}, R_E$: Note 2 Fig. 1 | t_{PLH} | All | | 150 | 330 | ns |
| Fall time | $C = 120\text{pF}, t_p = 1\mu\text{s}, R_E$: Note 2 Fig. 1 | t_f | All | | 12 | | ns |
| Data Rate | | | All | | 5 | | MHz |

| ISOLATION CHARACTERISTICS | | | | | | |
|--------------------------------|--|-----------|-----------|------|-----|------------|
| Parameters | Test Conditions | Symbol | Min | Typ* | Max | Units |
| Input-Output Isolation Voltage | $f = 60 \text{ Hz}, t = 1 \text{ sec.}$ | V_{ISO} | 7500 | | | V_{PEAK} |
| Isolation Capacitance | $V_{I-O} = 0\text{V}, f = 1 \text{ MHz}$ | C_{ISO} | | 0.4 | 0.6 | pF |
| Isolation Resistance | $V_{I-O} = \pm 500 \text{ VDC}$ | R_{ISO} | 10^{11} | | | Ω |

*Typical values at $T_A = 25^\circ\text{C}$

NOTES:

- Maximum $I_{F(ON)}$ is the maximum current required to trigger the output. For example, a 3.2mA maximum trigger current would require the LED to be driven at a current greater than 3.2mA to guarantee the device will turn on. A 10% guard band is recommended to account for degradation of the LED over its lifetime. The maximum allowable LED drive current is 30mA.
- H11N1: $R_E = 910\Omega$
H11N2: $R_E = 560\Omega$
H11N3: $R_E = 240\Omega$

H11N1-M

H11N2-M

H11N3-M

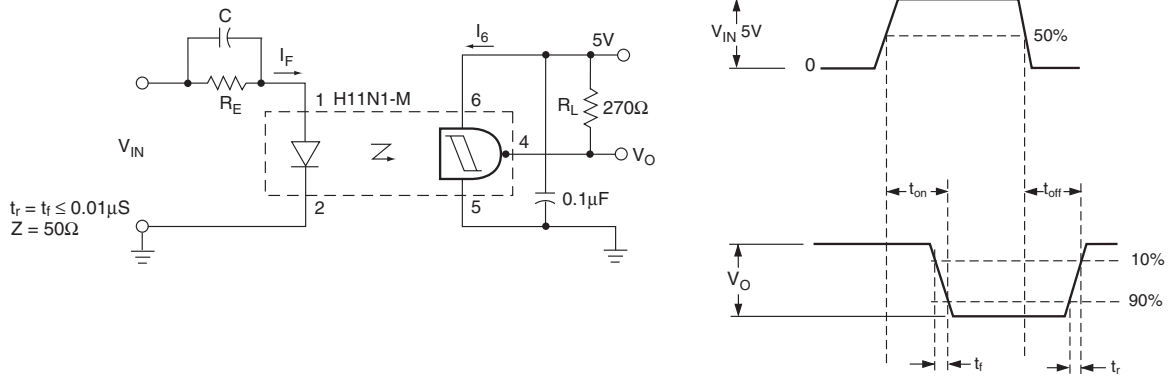


Figure 1. Switching Test Circuit and Waveforms

Figure 2. Transfer Characteristics

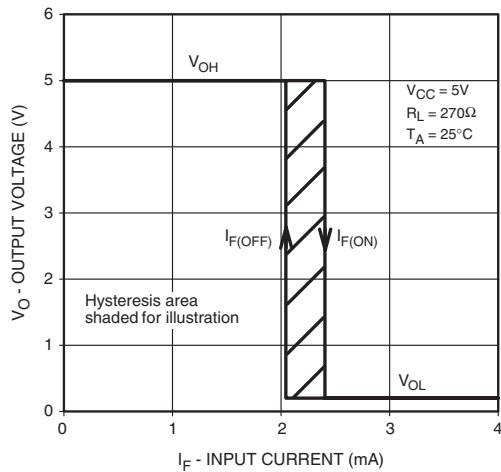


Figure 3. Threshold Current vs. Supply Voltage

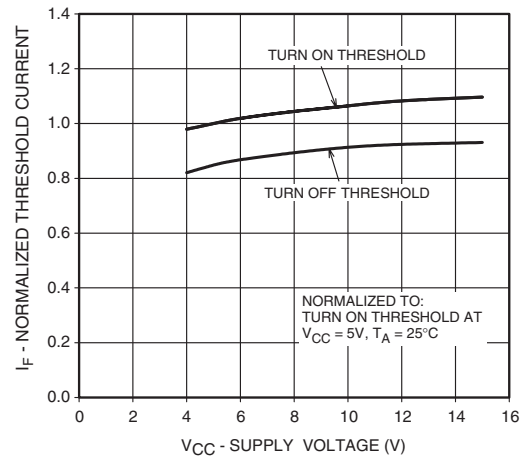


Figure 4. Threshold Current vs. Temperature

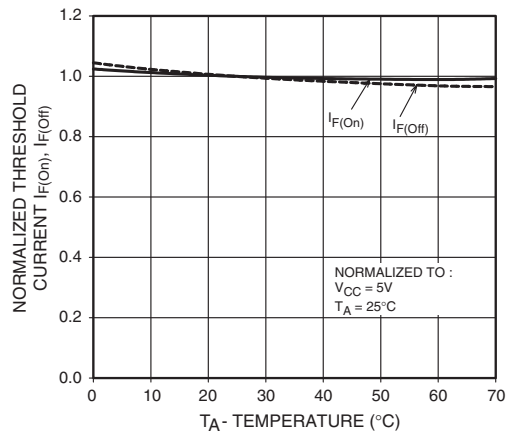
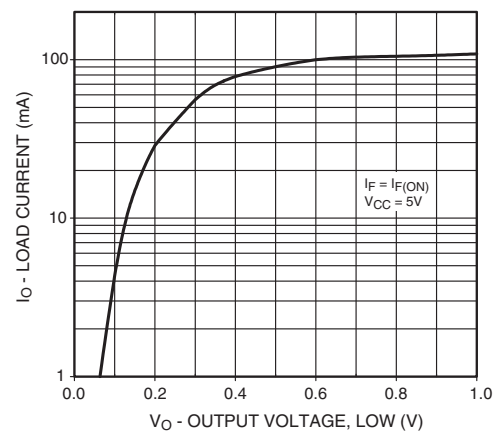


Figure 5. Load Current vs. Output Voltage



H11N1-M

H11N2-M

H11N3-M

Figure 6. Supply Current vs. Supply Voltage

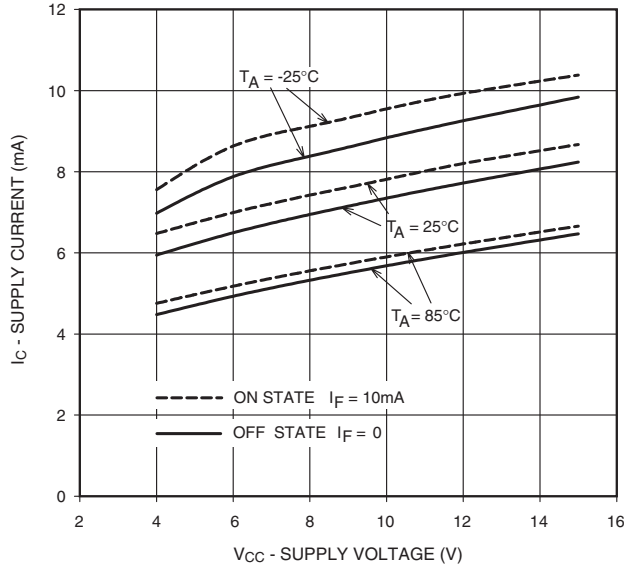
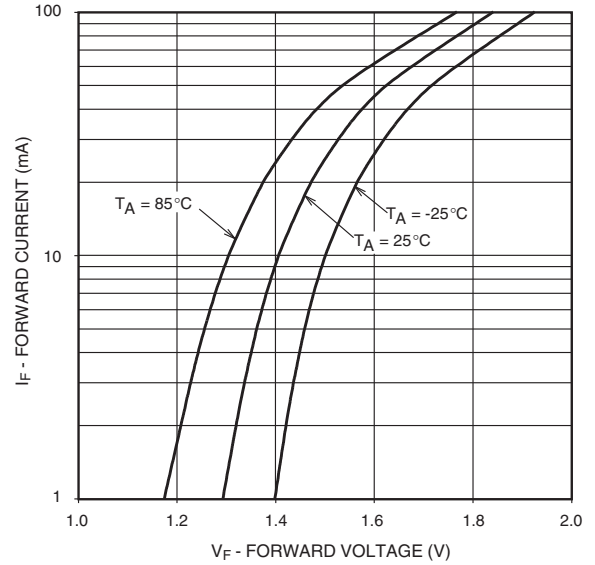


Figure 7. LED Forward Voltage vs. Forward Current

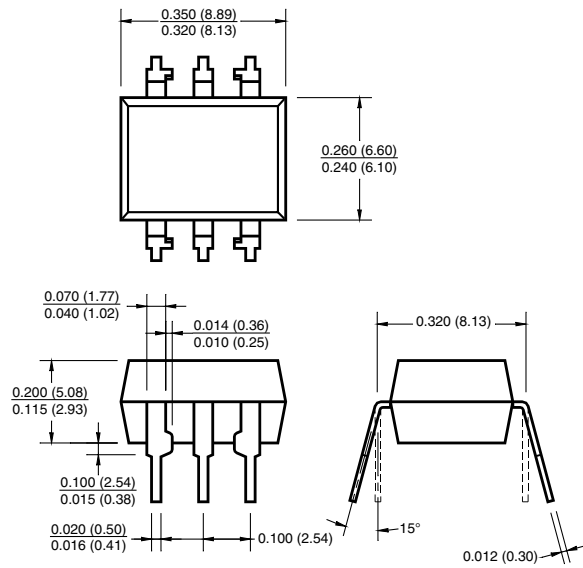


H11N1-M

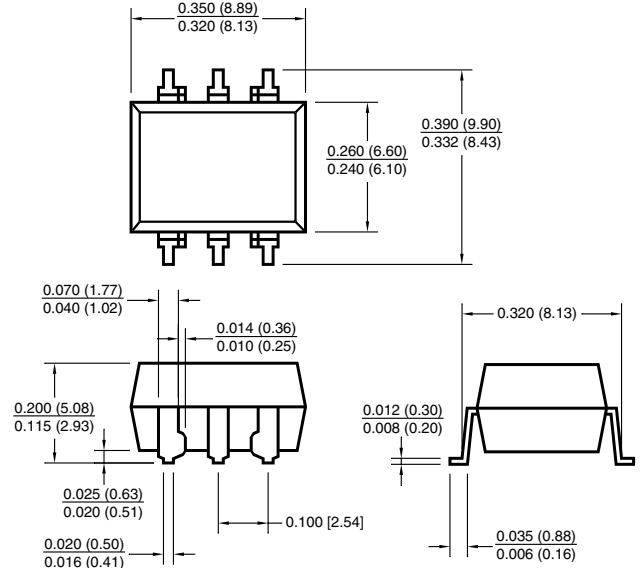
H11N2-M

H11N3-M

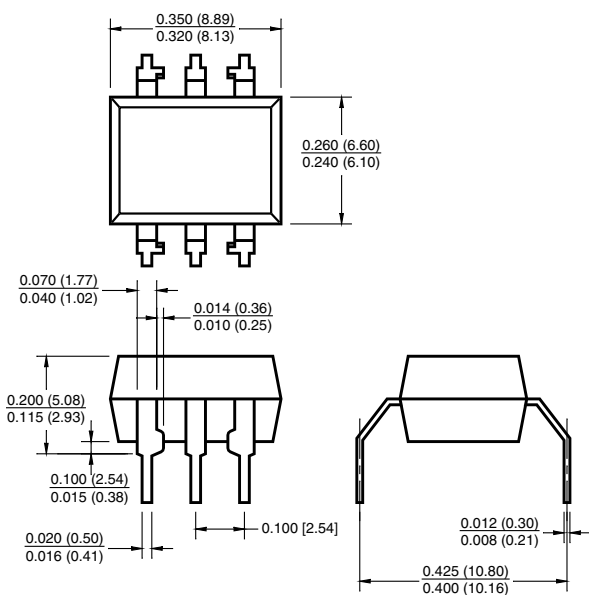
Package Dimensions (Through Hole)



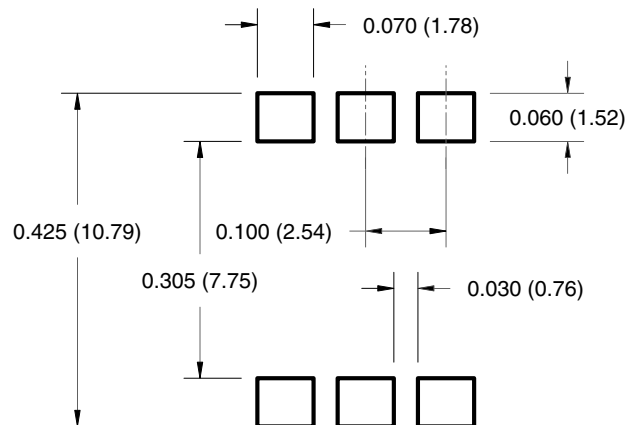
Package Dimensions (Surface Mount)



Package Dimensions (0.4" Lead Spacing)



Recommended Pad Layout for Surface Mount Leadform



H11N1-M

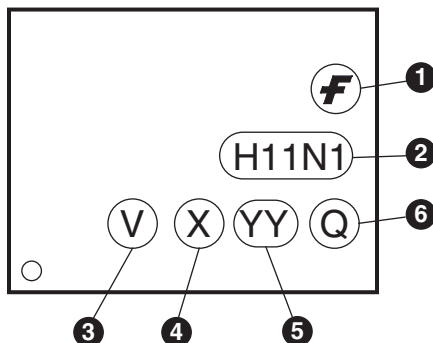
H11N2-M

H11N3-M

ORDERING INFORMATION

| Option/Order Entry Identifier | Description |
|-------------------------------|--------------------------------------|
| S | Surface Mount Lead Bend |
| SR2 | Surface Mount; Tape and reel |
| T | 0.4" Lead Spacing |
| V | VDE 0884 |
| TV | VDE 0884, 0.4" Lead Spacing |
| SV | VDE 0884, Surface Mount |
| SR2V | VDE 0884, Surface Mount, Tape & Reel |

MARKING INFORMATION



| Definitions | |
|-------------|--|
| 1 | Fairchild logo |
| 2 | Device number |
| 3 | VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table) |
| 4 | One digit year code, e.g., '3' |
| 5 | Two digit work week ranging from '01' to '53' |
| 6 | Assembly package code |

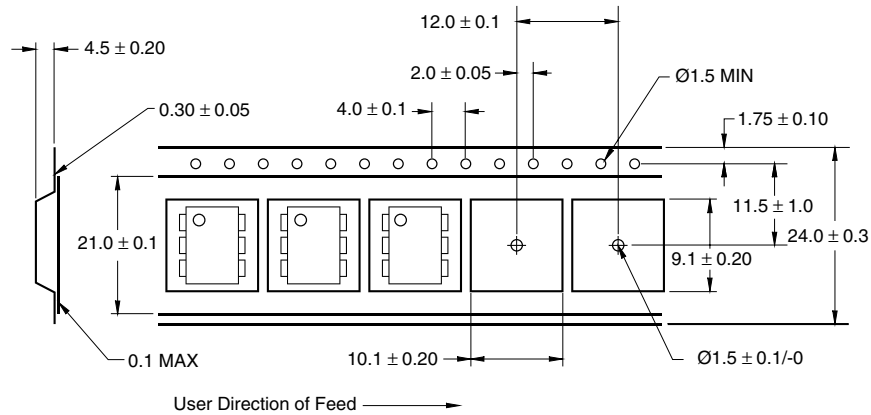
*Note – Parts that do not have the 'V' option (see definition 3 above) that are marked with date code '325' or earlier are marked in portrait format.

H11N1-M

H11N2-M

H11N3-M

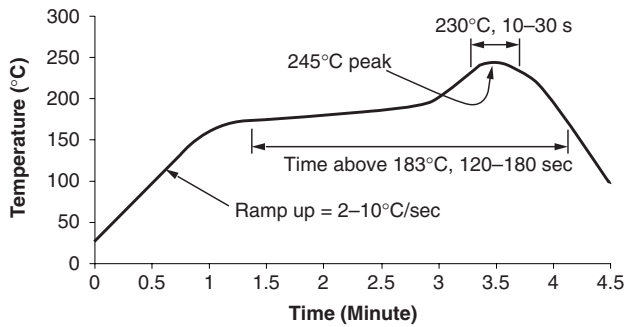
Carrier Tape Specifications



NOTE

All dimensions are in inches (millimeters)

Reflow Profile (White Package, -M Suffix)



- Peak reflow temperature: 245°C (package surface temperature)
- Time of temperature higher than 183°C for 120-180 seconds
- One time soldering reflow is recommended

H11N1-M

H11N2-M

H11N3-M

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